



# Megapixels @ Megahertz

## AGIPD Detectors for the European XFEL and beyond

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## The AGIPD System

European XFEL  
Single molecule imaging  
Requirements

## AGIPD 1.1 Readout ASIC

Architecture  
Dynamic gain switching  
Performance

## AGIPD Detector systems gen. 1: SPB & MID endstations

Overview  
First user experiments  
Results

## AGIPD Detector Systems gen. 2: SFX & HiBEF endstations

Readout boards  
Optical communications  
Cooling and mechanics

## New ASICS: AGIPD 1.2 and ecAGIPD

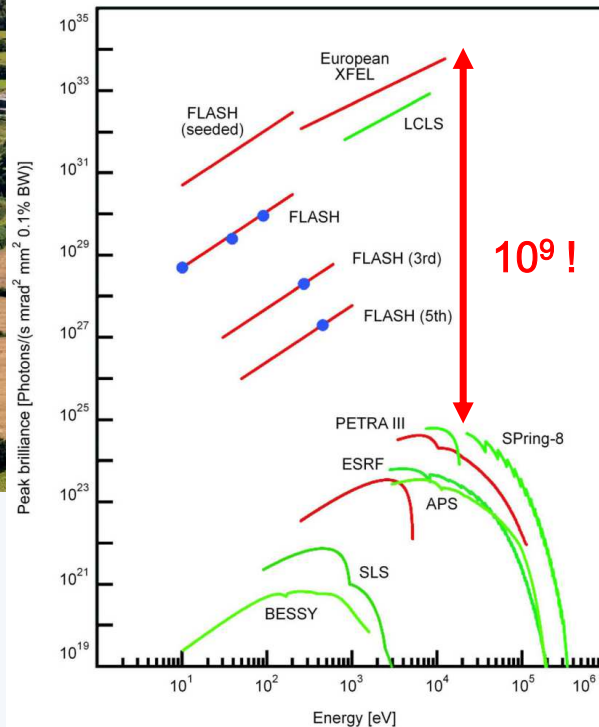
AGIPD 1.2  
Electron-collecting AGIPD  
AGIPD06 demonstrator

## Beyond AGIPD

## Conclusion

Summary  
Outlook

# European XFEL properties



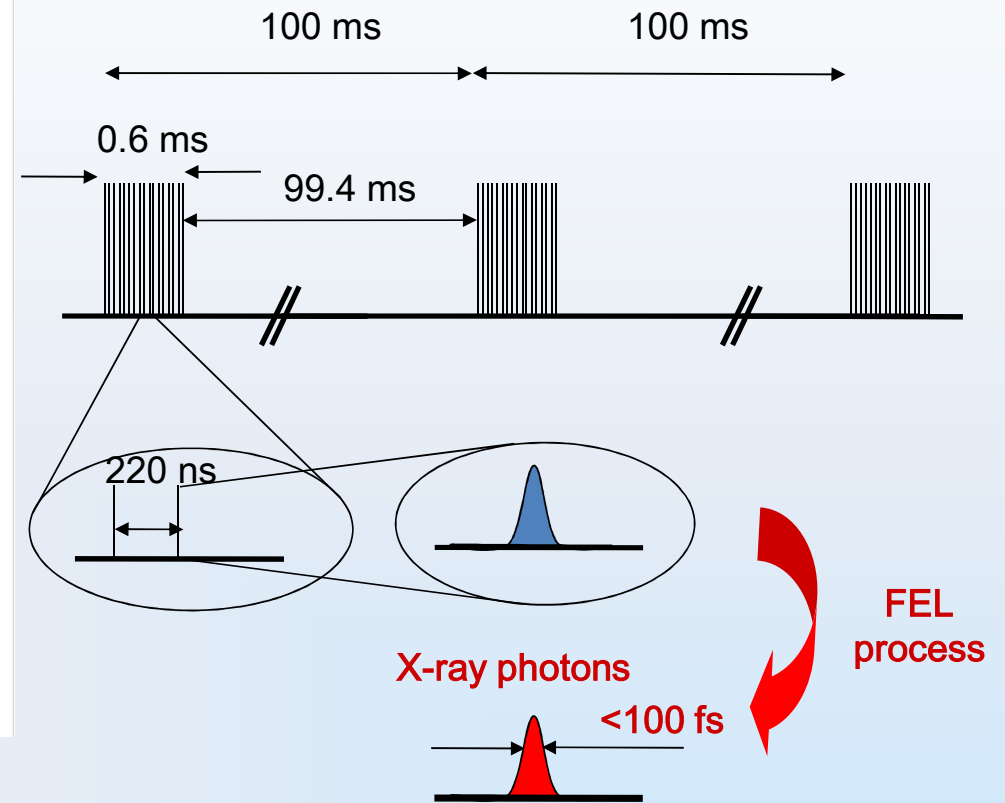
$E_\gamma = 250\text{eV} \dots 12\text{keV}$

av. Rate:

- 27kHz XFEL
- 120Hz LCLS
- 60Hz SCSS

Detectors:

- LPD (500 $\mu\text{m}$  x 500 $\mu\text{m}$ ) - 1Mpix installed
- AGIPD (200 $\mu\text{m}$  x 200 $\mu\text{m}$ ) - 2  $\times$  1Mpix installed, 4Mpix & 1Mpix under construction
- DSSC (230 $\mu\text{m}$  x 200 $\mu\text{m}$  hexagonal) - 1Mpix under construction



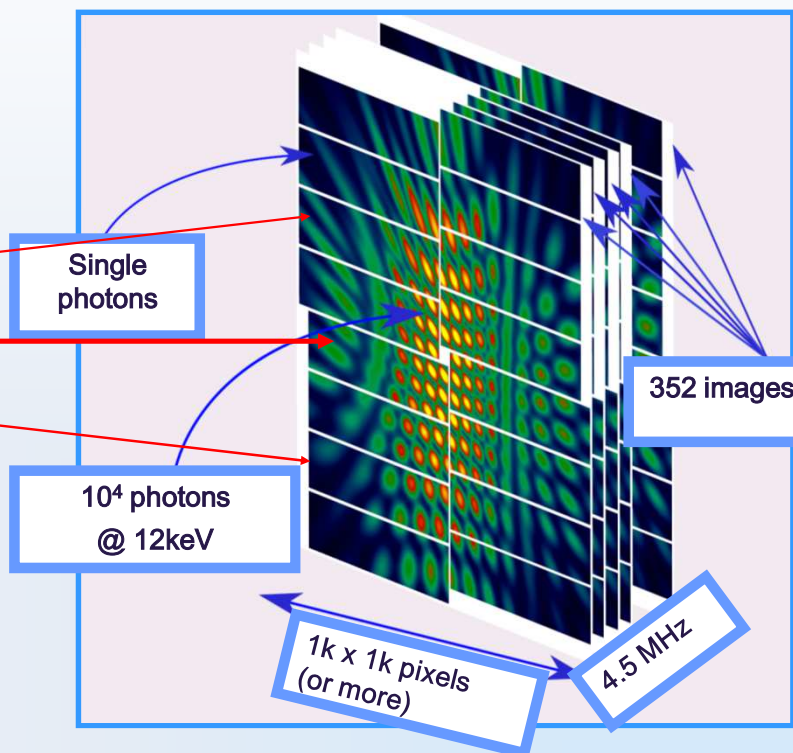
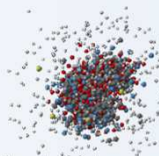
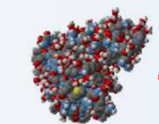
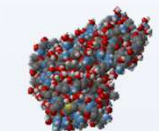
# AGIPD Scientific Case: Single Molecule Imaging & SFX



Just before  
XFEL pulse

During the  
pulse

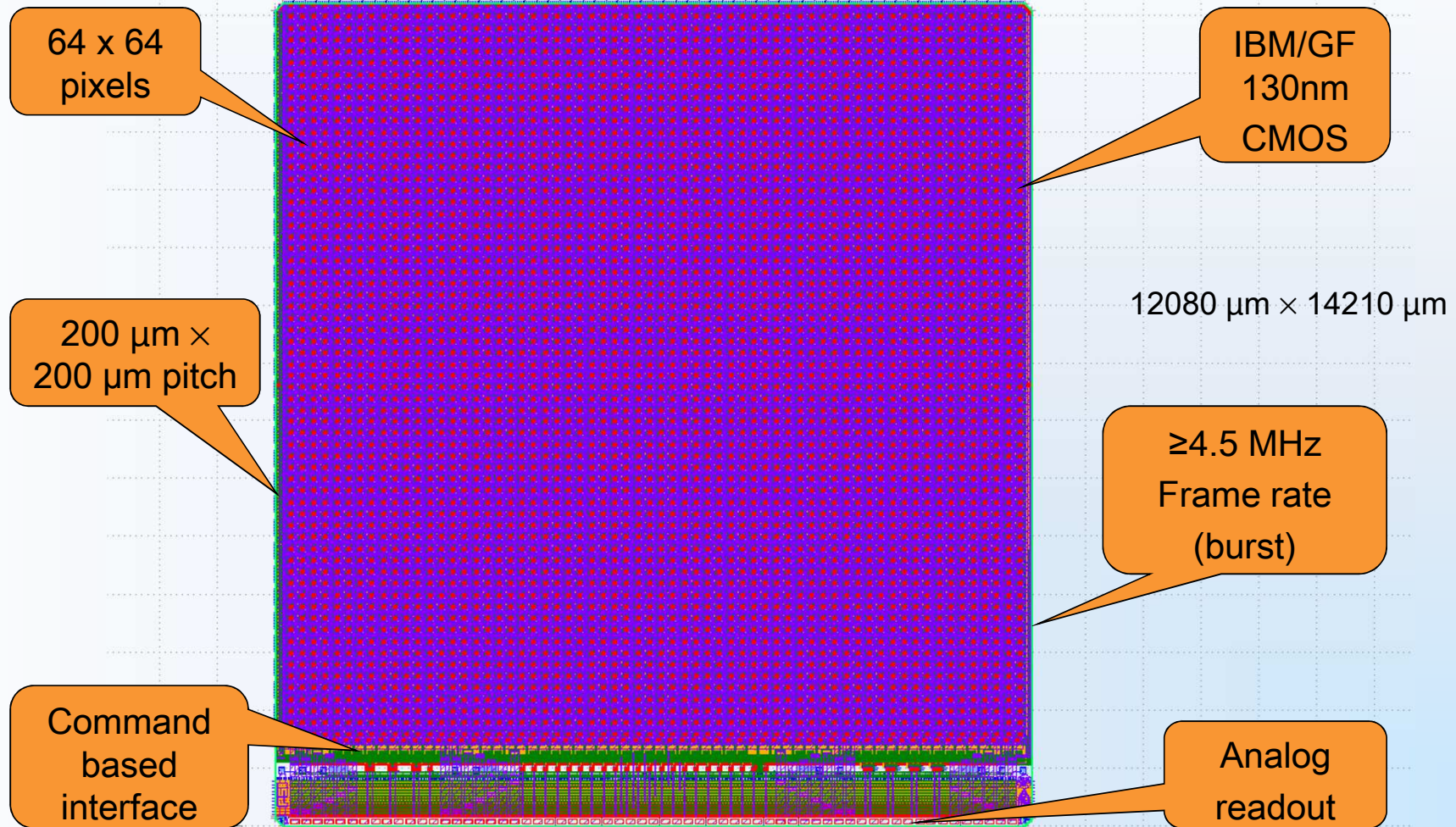
After pulse



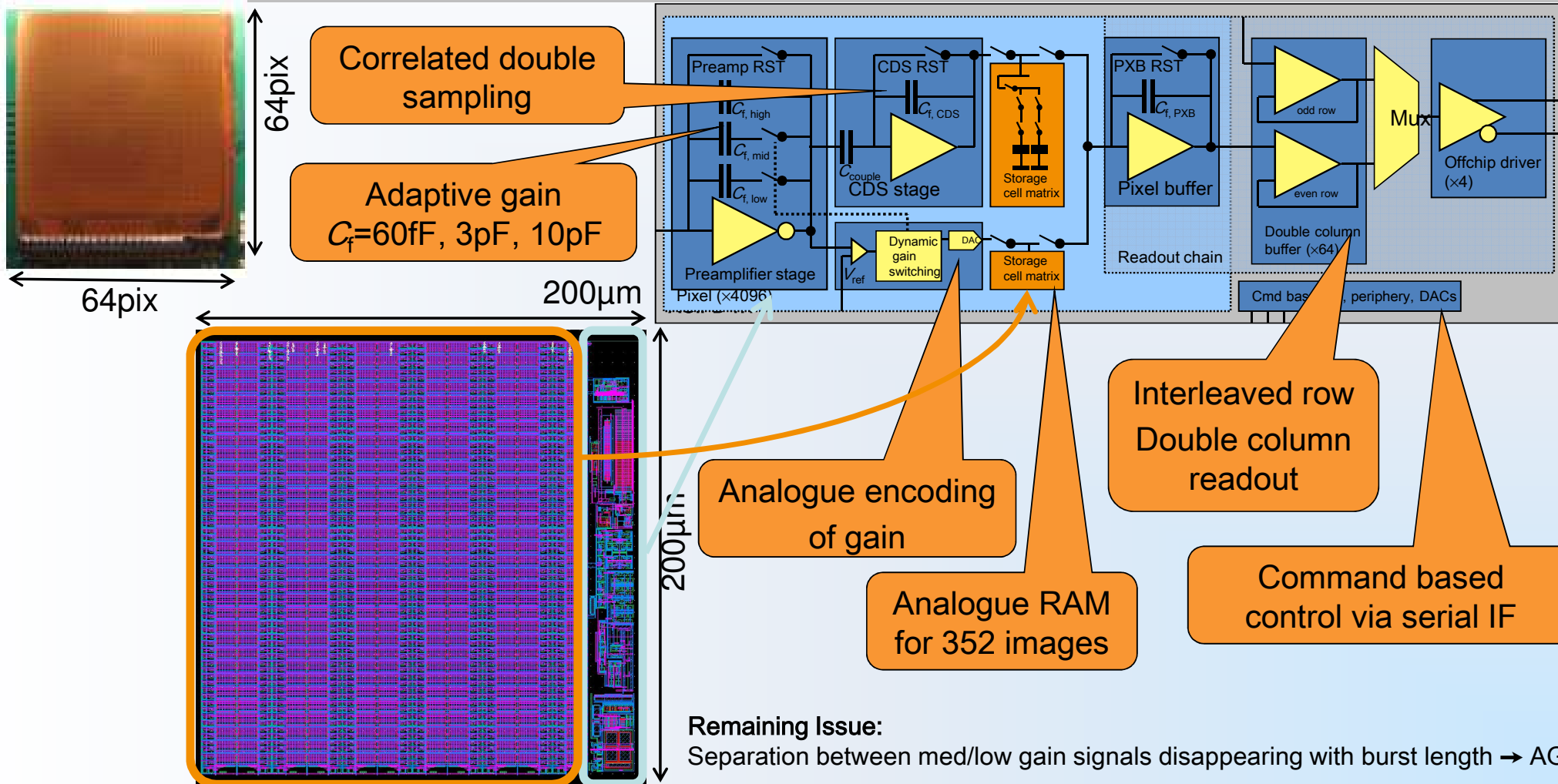
- Time structure of the photon signals
  - Pipelined architecture
  - Random access mode
    - External veto capability
- High radiation dose at small angles: 10<sup>4</sup> photons/(pixel shot)
- over 3 years: 1 GGy @sensor
  - Radiation damage of silicon sensor
  - Radiation damage of underlying electronics (>>10 MGy)
    - Radiation hard design

- 500 μm silicon sensor
- 200 μm square pixels
- Vacuum compatibility
- Detector with central hole

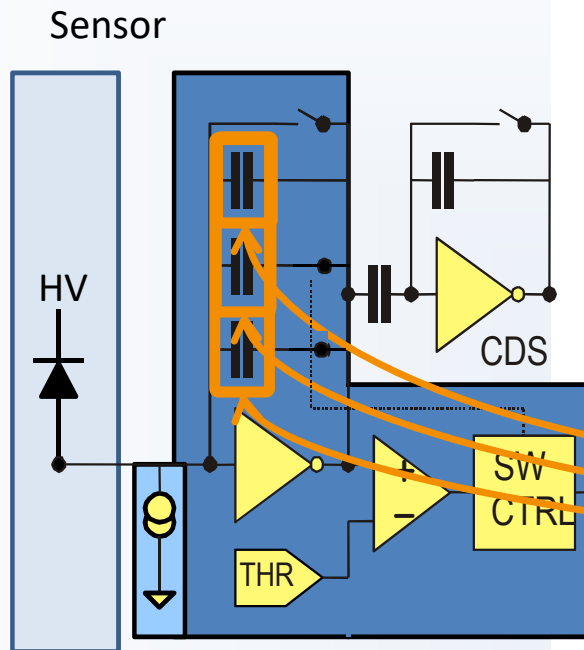
# AGIPD 1.1 ASIC



# AGIPD 1.1 ASIC



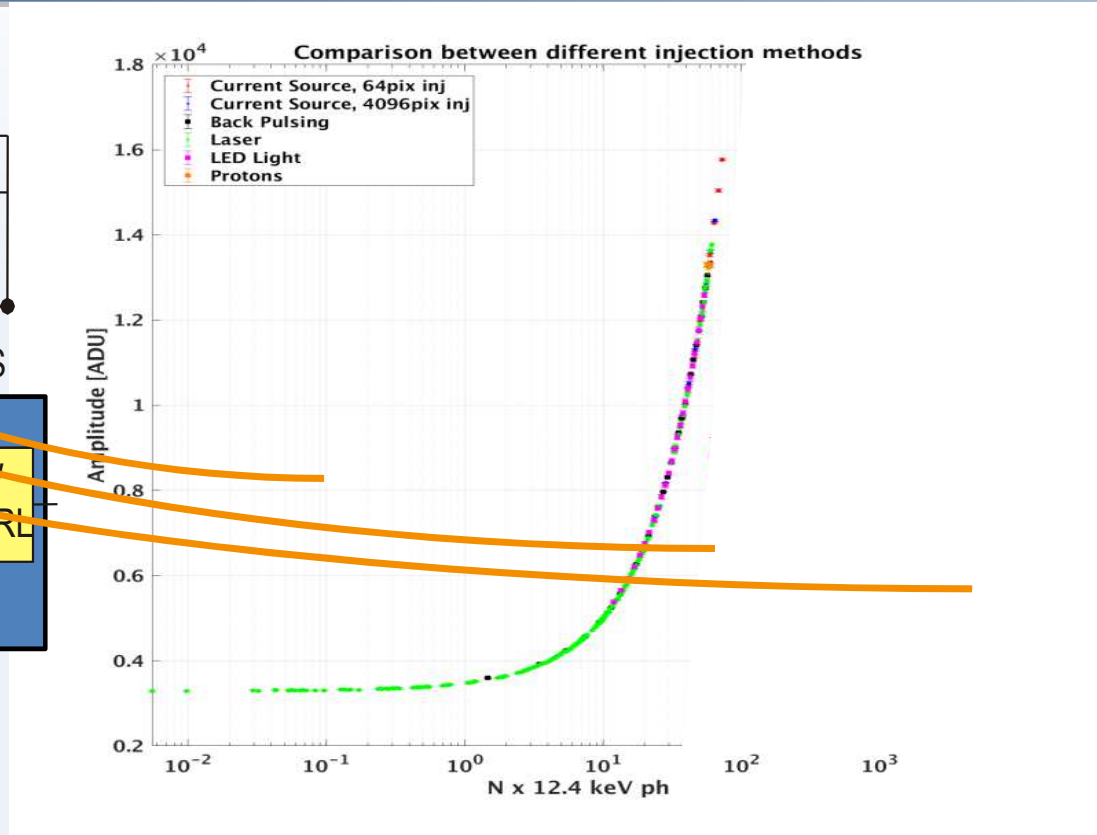
# Adaptive gain switching



Calibration circuitry

Adaptive gain amplifier

Line spectra covering all 3 gains with (1MeV) Protons@LABEC



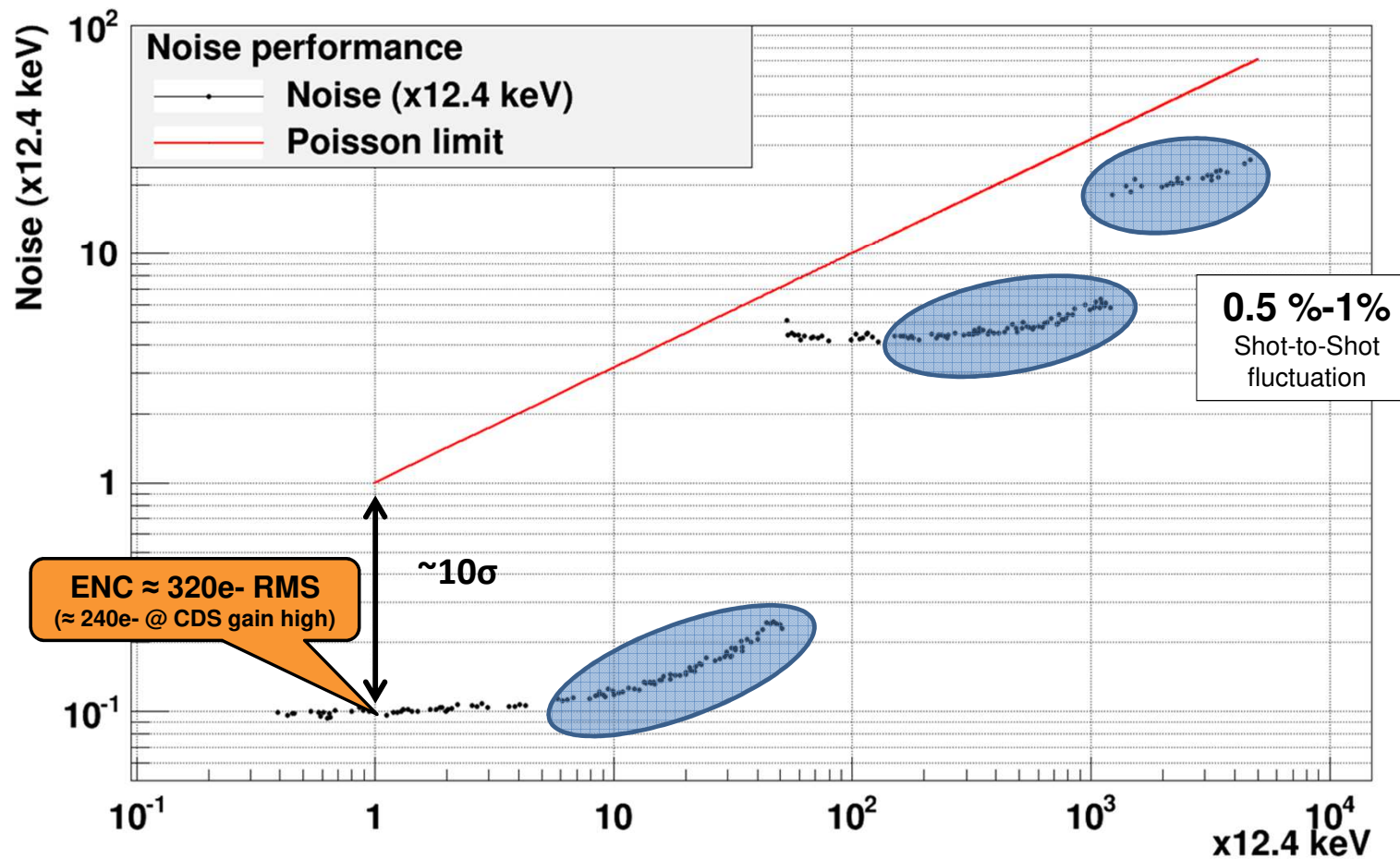
High gain: 50-80 Photons with single photon sensitivity.

Low gain: 5000 photons with linear gain +5000 photons with 1% nonlinearity.

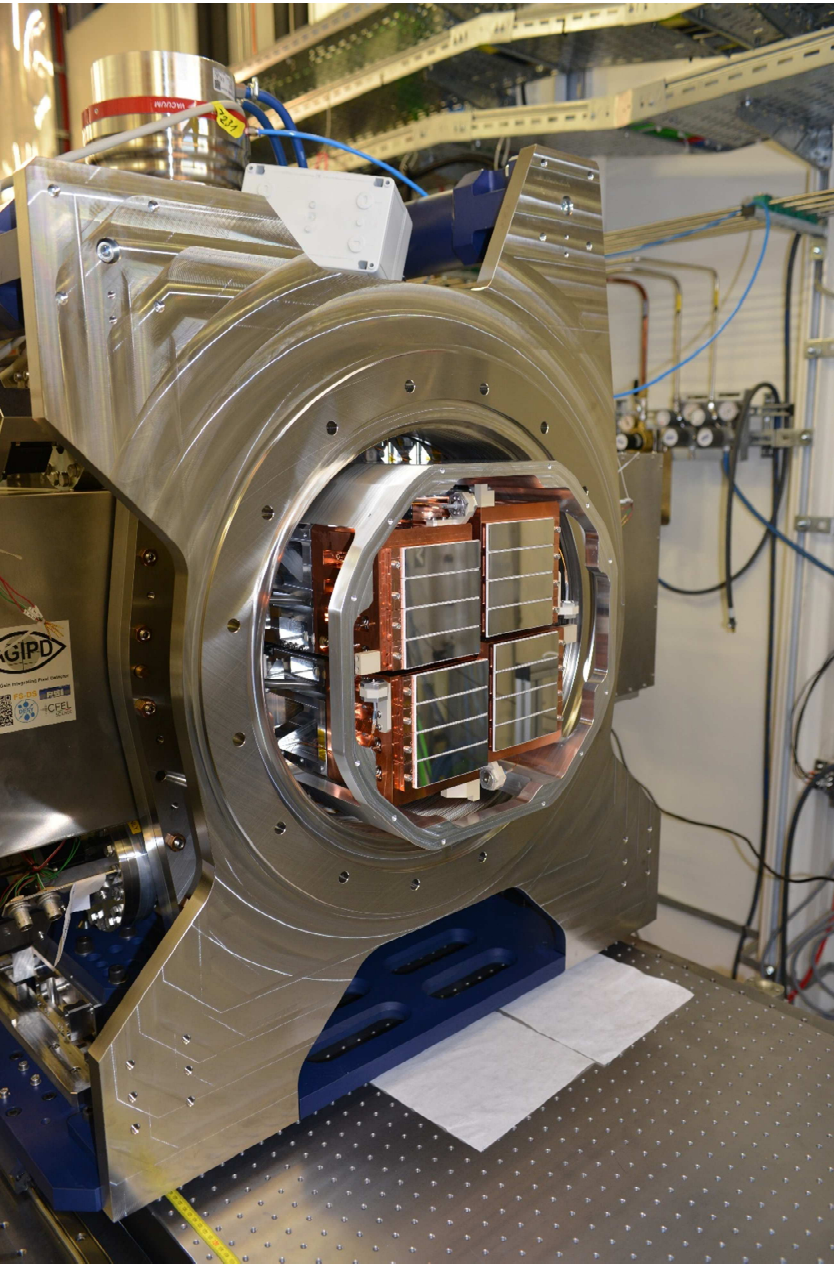
# AGIPD Detector noise



AGIPD1.0 - Chip 1 - Noise over Dynamic Range (x12.4 keV) - LASER (IR)





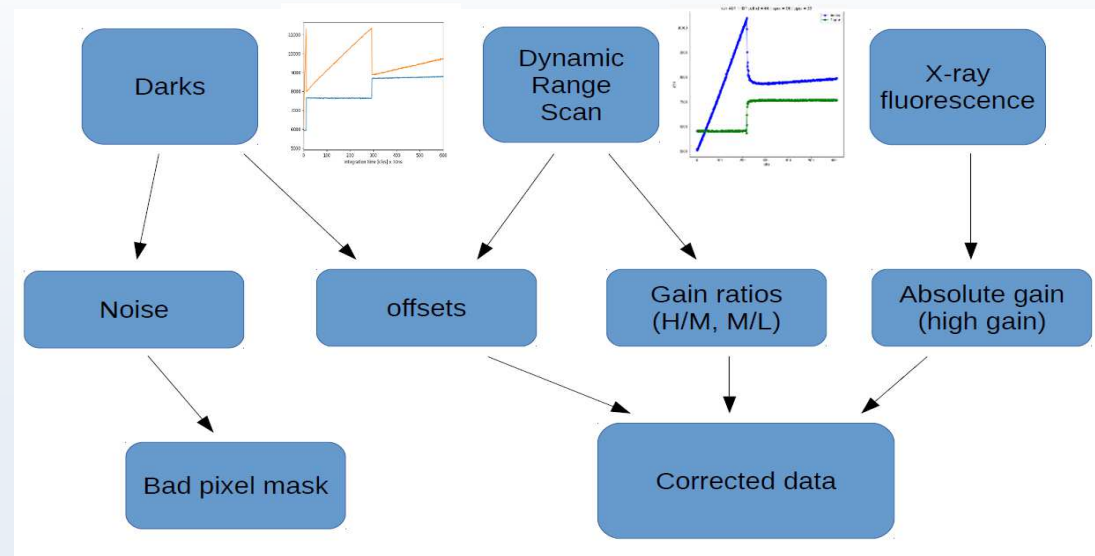
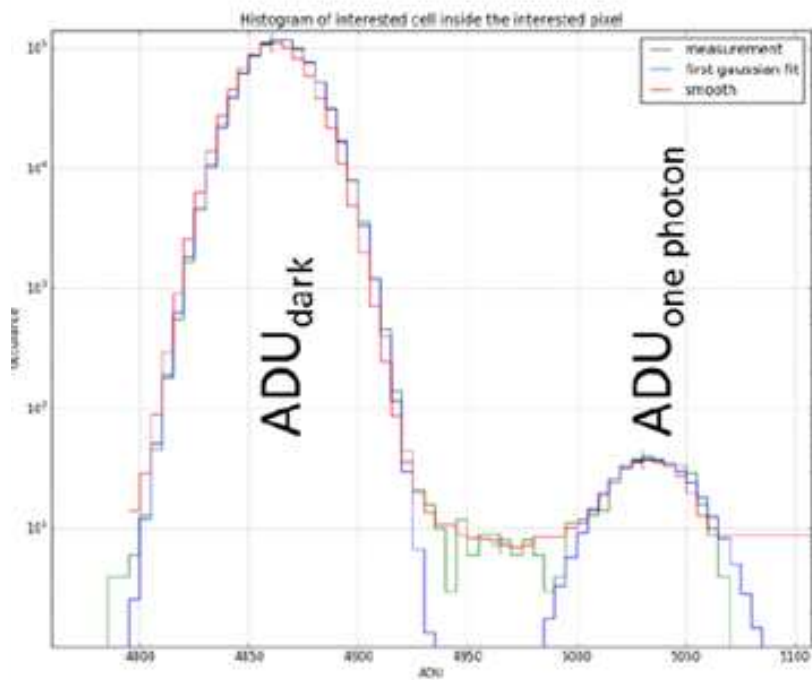


# AGIPD 1Mpix Systems: Calibration



Feed calibration framework with

- Pulsed capacitor dynamic range scans for all memory cells used
- Cu-K<sub>α</sub> data at XFEL
- Dark data for High and Medium gain level



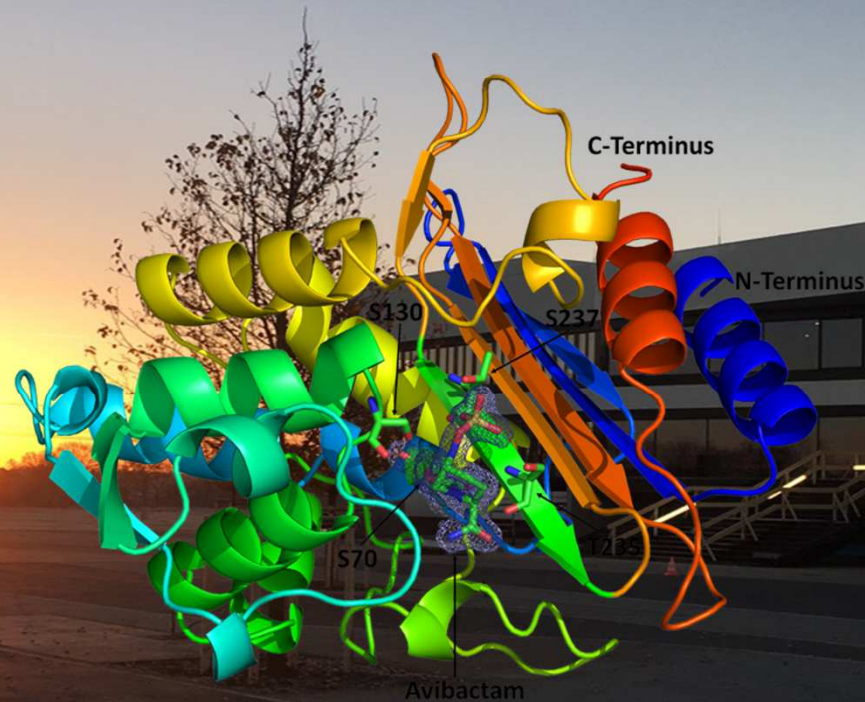
Calibration framework follows a modular concept and allows removing, adding and exchanging building blocks

- Huge number of fits!
- 65,536 pixels
- 352 memory cells
- 3 Gains + 3 Offsets
- $\approx 138,000,000$  fits / module
- 16 Modules  $\rightarrow 2.2 \times 10^9$  constants
- computation time, fit quality, non-constant fit ranges

### Time & Resources:

- DAQ:  $\leq 2$ h
  - @ European XFEL
- Calibration:  $\leq 4$ h
  - on DESY Maxwell cluster

Resolved structure of  
CTX-M-14  $\beta$ -lactamase

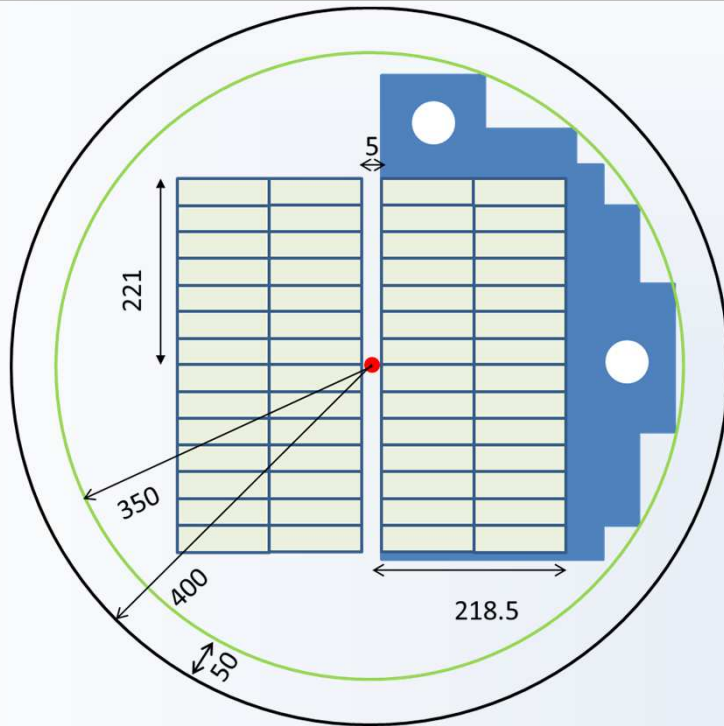


XFEL-2012 collaboration

“Megahertz serial crystallography” [Nat Communications](#) 9(1), 4025 (2018)

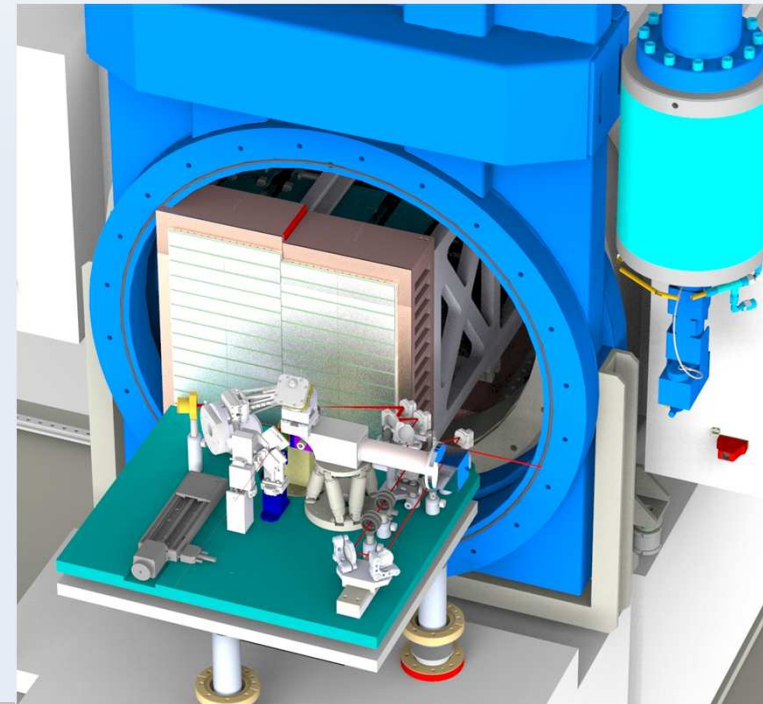
[doi:10.1038/s41467-018-06156-7](https://doi.org/10.1038/s41467-018-06156-7)

# AGIPD 4M Detector for SFX

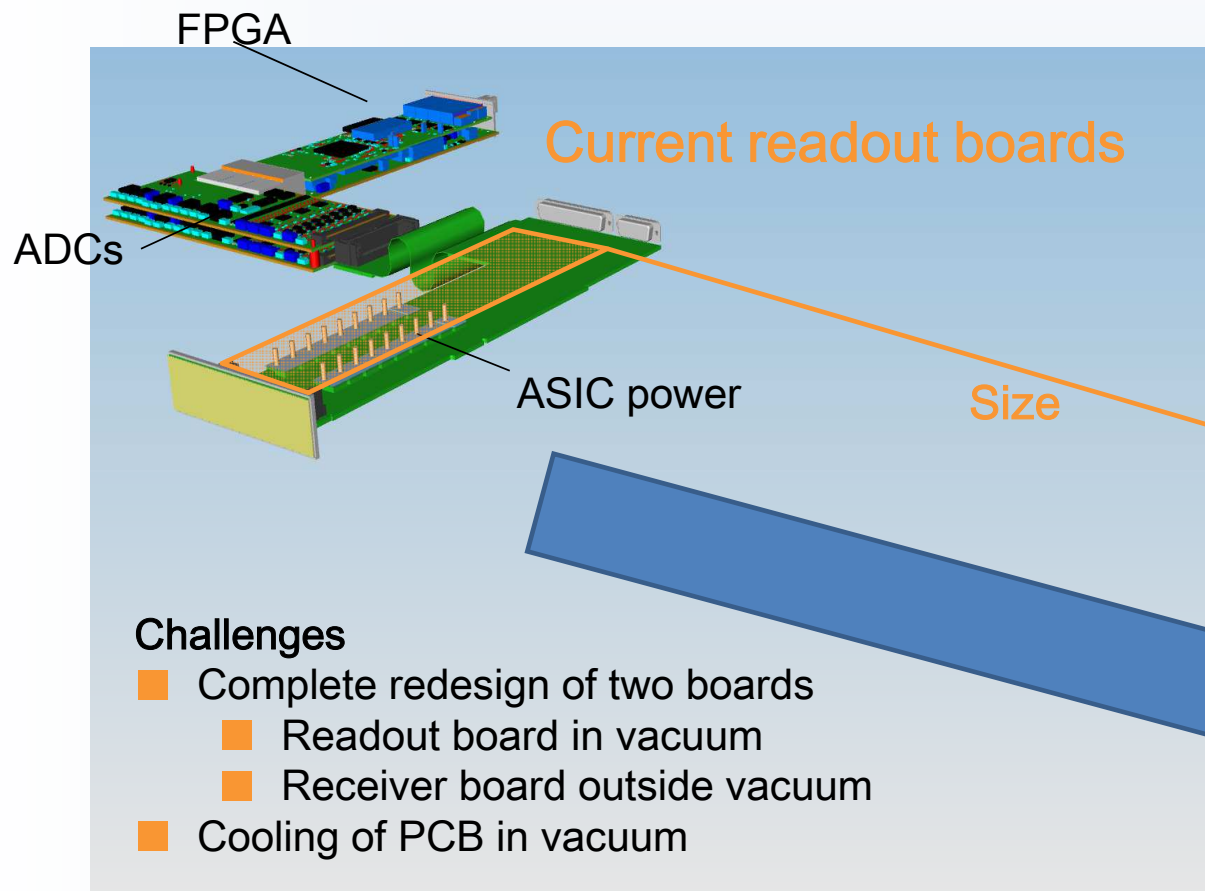


- In-vacuum z-motion
  - through gate valve
    - inner diameter 800mm
  - into sample chamber
  - travel range of 400 mm

- 4 x 14 Front-End-Modules, arranged in
  - 2 x 14 Double-Modules
- Two halves
  - 2 x 14 FEMs each
  - Independent in-vacuum x-motion



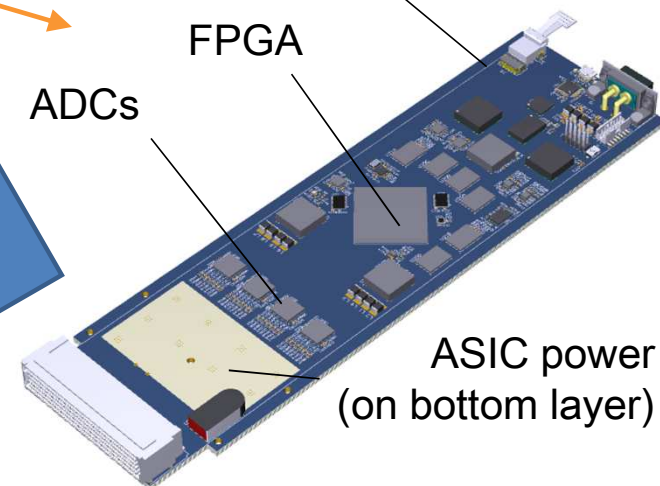
# AGIPD 4M Detector for SFX



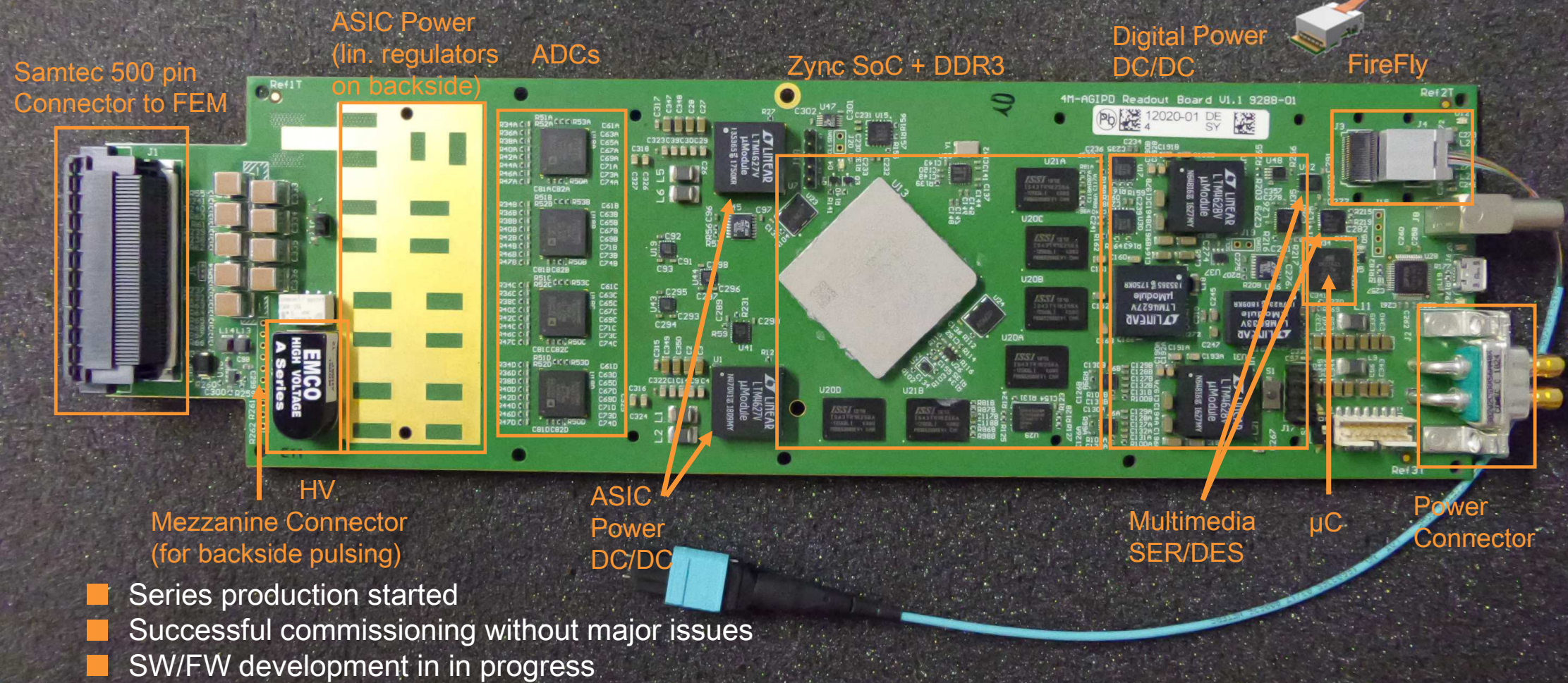
## Advantages

- Short analogue signal path
- Local DC/DC -> less power cables
- Control and DAQ completely based on optical data transmission

## New readout board

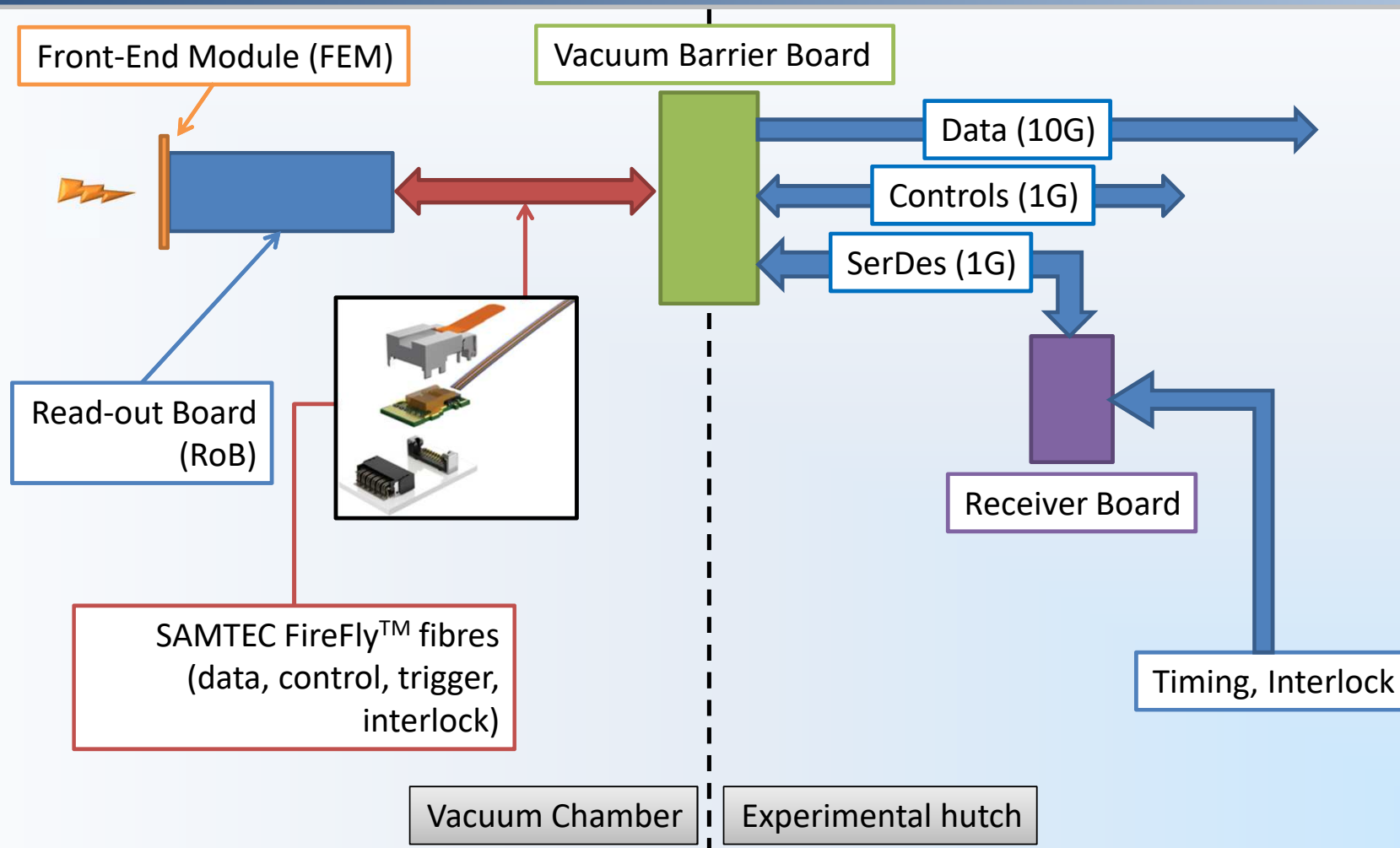


# AGIPD 4M Detector for SFX



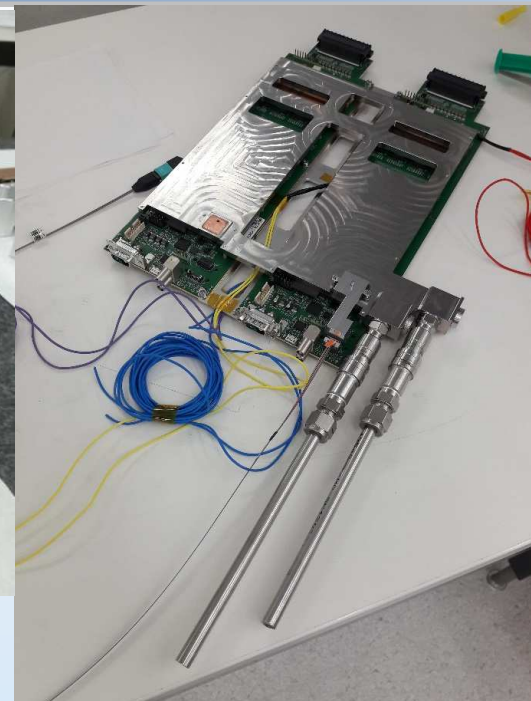
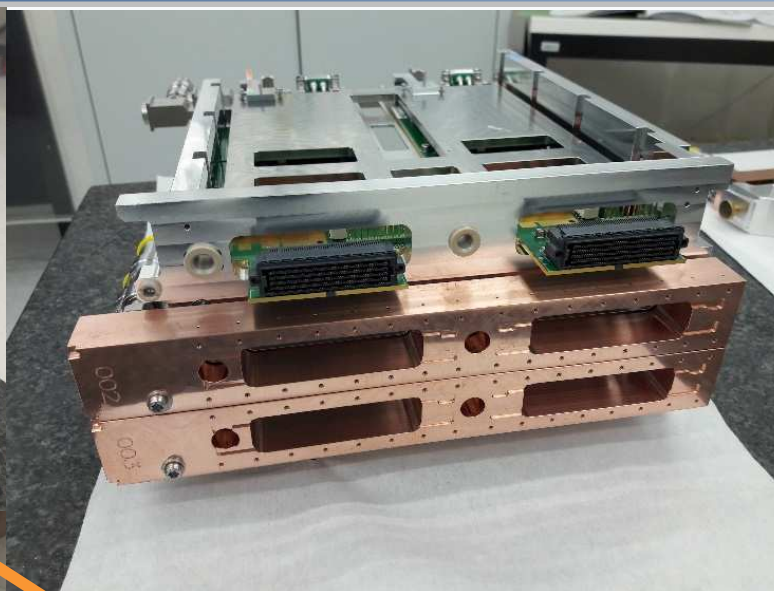
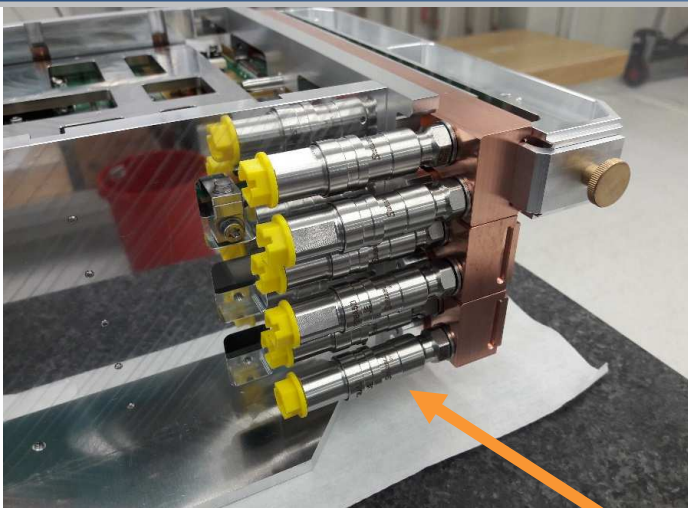
- Series production started
- Successful commissioning without major issues
- SW/FW development in progress

# AGIPD 4M Detector for SFX



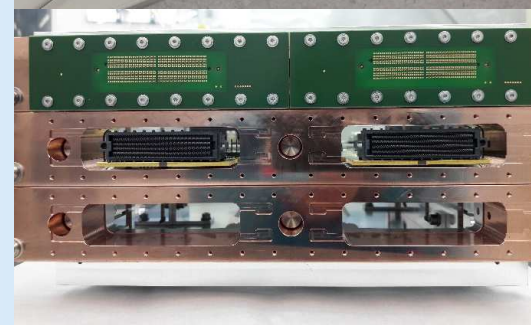
# AGIPD 4M Detector for SFX

## In-Vacuum Cooling



### Liquid Cooling of

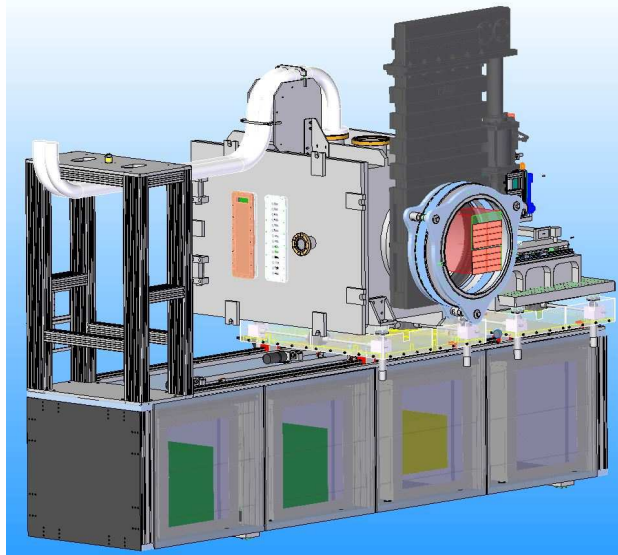
- Modules
  - Cooling channels in Copper frame
  - Coolant: Silicone oil
- Readout boards
  - Coolant: Water
- In-Vacuum connectors





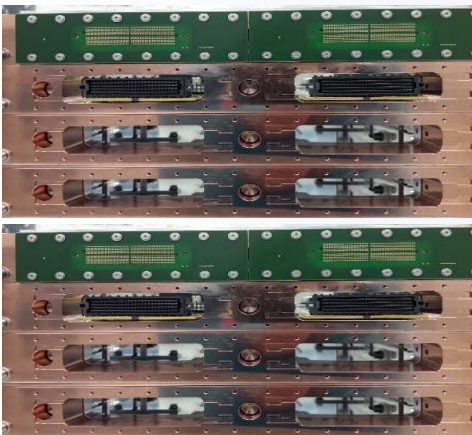
# AGIPD 1M Detector for HiBEF

@HED Endstation of European XFEL



The HiBEF (Helmholtz International Beamline for Extreme Fields) experiment @ EuXFEL needs a 1Mpix detector for  $E_{ph} \geq 25\text{keV}$

- The existing AGIPD detector collects positive charges (holes)
  - Easier to realise radiation hard sensors
  - Slower – less demanding to handle large charges (circuit wise)
- AGIPD is not suitable for experiments with photons above  $\sim 15\text{keV}$ 
  - The Silicon sensor gets inefficient  $\sim 15\text{keV}$
- High-Z Semiconductors, esp. GaAs promise efficient sensors for  $E_{ph} \geq 25\text{keV}$
- Composite (III/V) Semiconductors feature relatively short charge carrier lifetimes
- Collection of Electrons (i.e. the fast component) is required

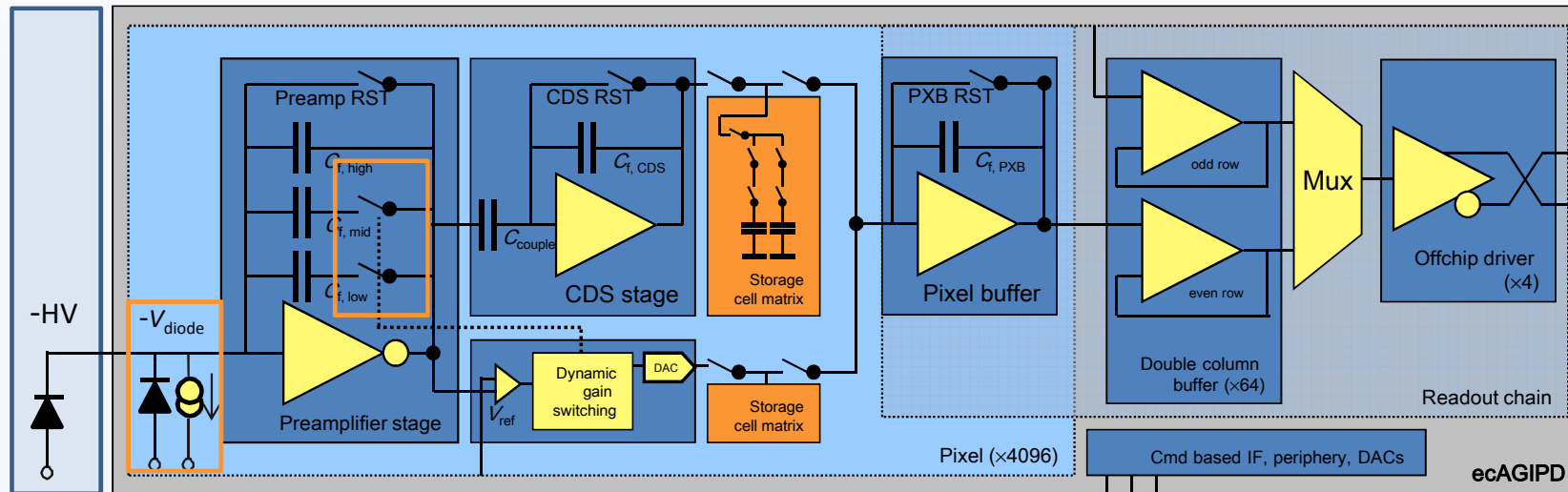


# New ASICs: AGIPD 1.2 and ecAGIPD



## AGIPD 1.2:

- Improve Med $\leftrightarrow$ Low gain detection
- Modified storage cells
- Taped out Aug. 2018
- Back mid April 2019
- Shows  $\approx$  30% better 'gain separation' from wafer testing (no burst readout)
- Module production at IZM and ADVACAM under way



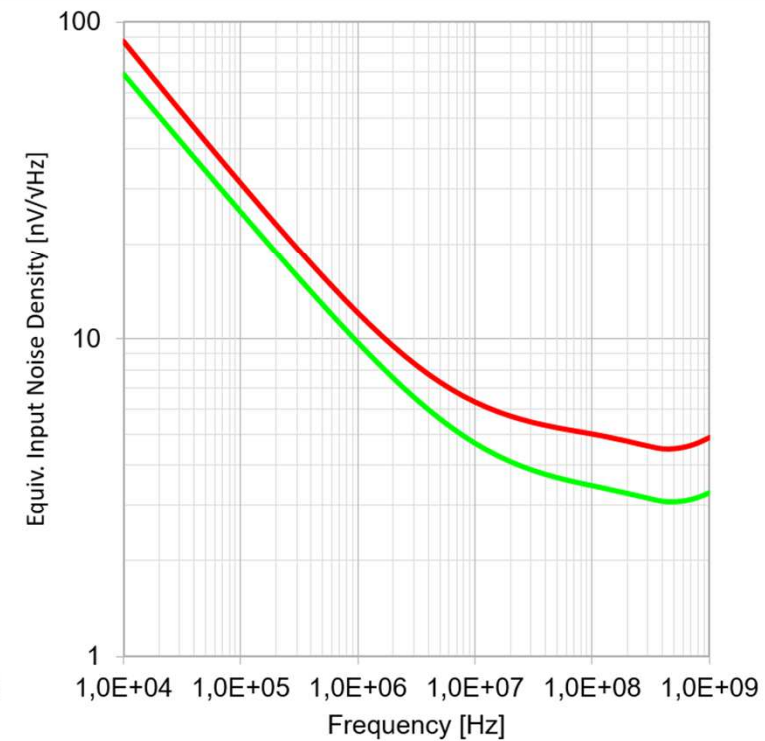
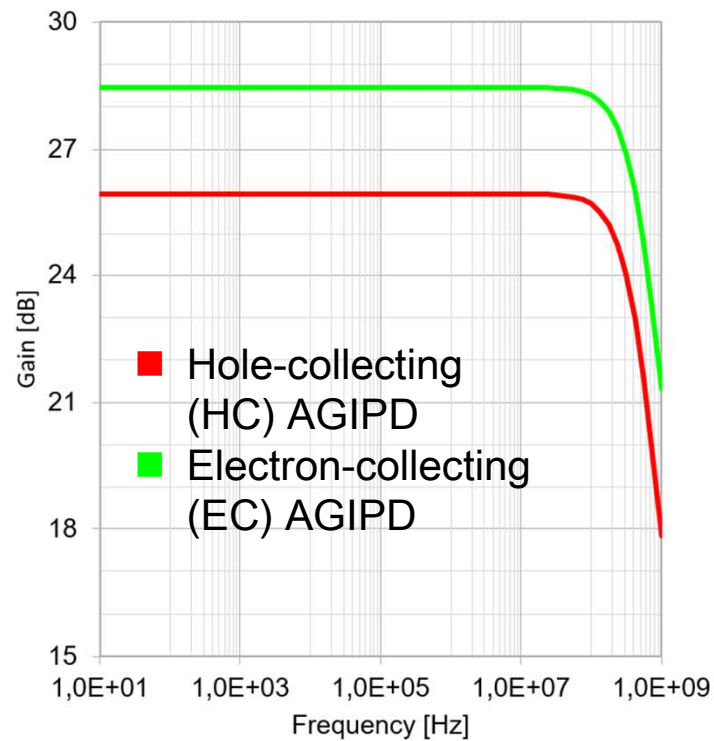
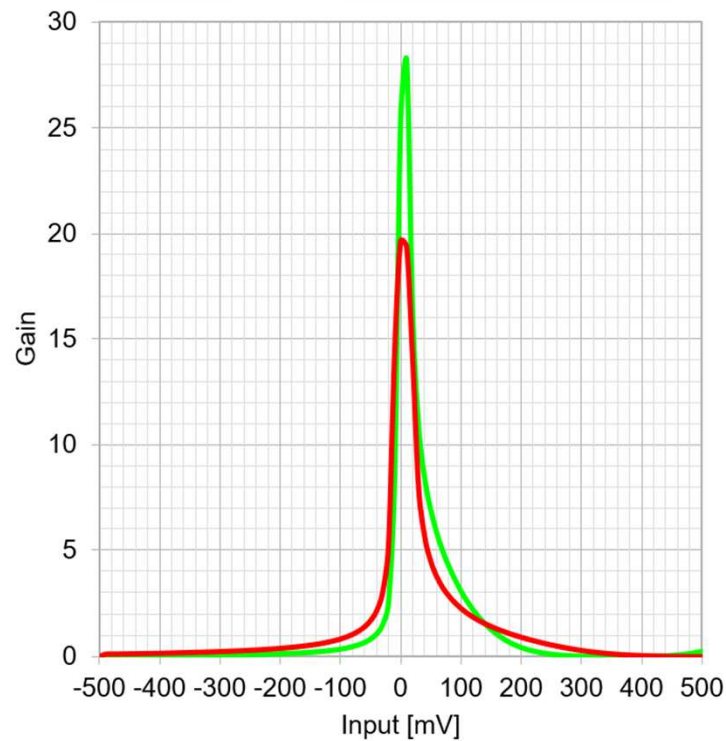
- Triple-well structure at negative ( $V_{diode} \sim -1V$ ) voltage containing
  - Input protection diode
  - Current source for test stimulus = current mirror driven by existing source
  - Feedback switches
- Modified Preamp
  - New baseline at  $\sim 400mV$
- Discriminator of opposite polarity
- Changed gain encoding
  - Hi  $\leftrightarrow$  Lo
- Swapped output pads

ecAGIPD

# ecAGIPD-Preamp



- Higher open-loop gain (29 vs. 19)
- Same bandwidth (-3dB @ ~500MHz)
- Same noise density and power consumption



# ecAGIPD: AGIPD06 Prototype



Virtuoso® Layout Editing: AGIPD06 agipd06\_top layout Version:2-CheckedOut (on cfield-trunk1)

X: 4198.61 Y: 4160.34 (F) Select: 0 DRD: OFF dX: dY: Dist: Cmd:

Tools Design Window Create Edit Verify Connectivity Options Routing Migrate Design Manager Calibre

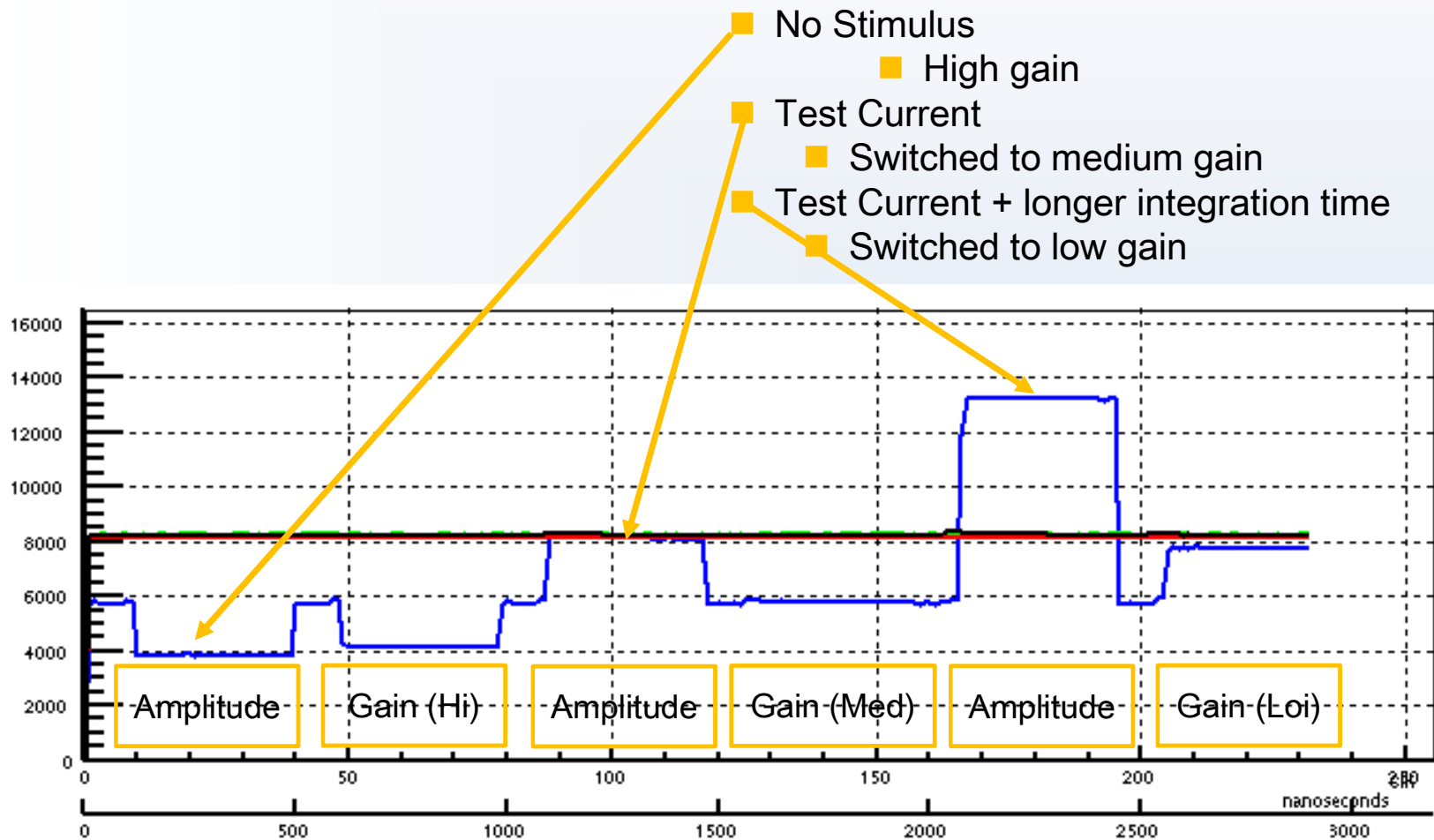
mouse L: mouseSingleSelectPt N: leftMousePopUp() R: hiZoomIn()

- 16x16 pixels
- SR (i.e. no) periphery
- RX outside guarding to make TW134 happy...

Modifications to investigate 'gain bit' issues:

- Mem cells like in AGIPD 1.2
- Order of mem row & column switches reversed

# ecAGIPD: AGIPD06 Prototype



## Preliminary results:

- EC Preamp works
- Noise  $\approx 282e^-$   
( $= \sqrt{340^2e^- - 182^2e^-}$ )
- Gain switching works
- Test stimuli work:
  - Pulsed capacitor
  - Current source
- $\approx 20\%$  better 'gain separation' of modifies storage cells

## Issues:

- Baseline jump when gain-switching
  - Charge injection?
  - X-talk?
- Excess noise

European XFEL operation will change in the 2<sup>nd</sup> half of the 2020s. Currently 2 additional operation modes are foreseen:

- CW operation at 100kHz
- 'Long Pulse' mode with  $\leq 200\text{kHz}$  in 500ms bursts, i.e. 50% duty cycle

On the same time scale the PETRA IV DLLS will become available.

- Intensity will allow to record complete diffraction patterns in  $\approx 10\mu\text{s}$

Plans for a possible successor of AGIPD are

- $\geq 100\text{kHz}$  (CW) imager
- $100\ \mu\text{m} \times 100\ \mu\text{m}$  Pixels
- Dynamic gain switching
- In-pixel (group) ADC
- (Very) Limited pipeline for burst mode
- High-speed serial link I/O



# Going Faster: With Analogue Readout



Ingredients (1<sup>st</sup> order):  $t = \frac{1}{f_{\text{ADC}}}$

Digitisation with  $n$  bits

at a rate of  $f_{\text{ADC}}$

$$2^{-n} \leq e^{-\frac{t}{\tau}}$$

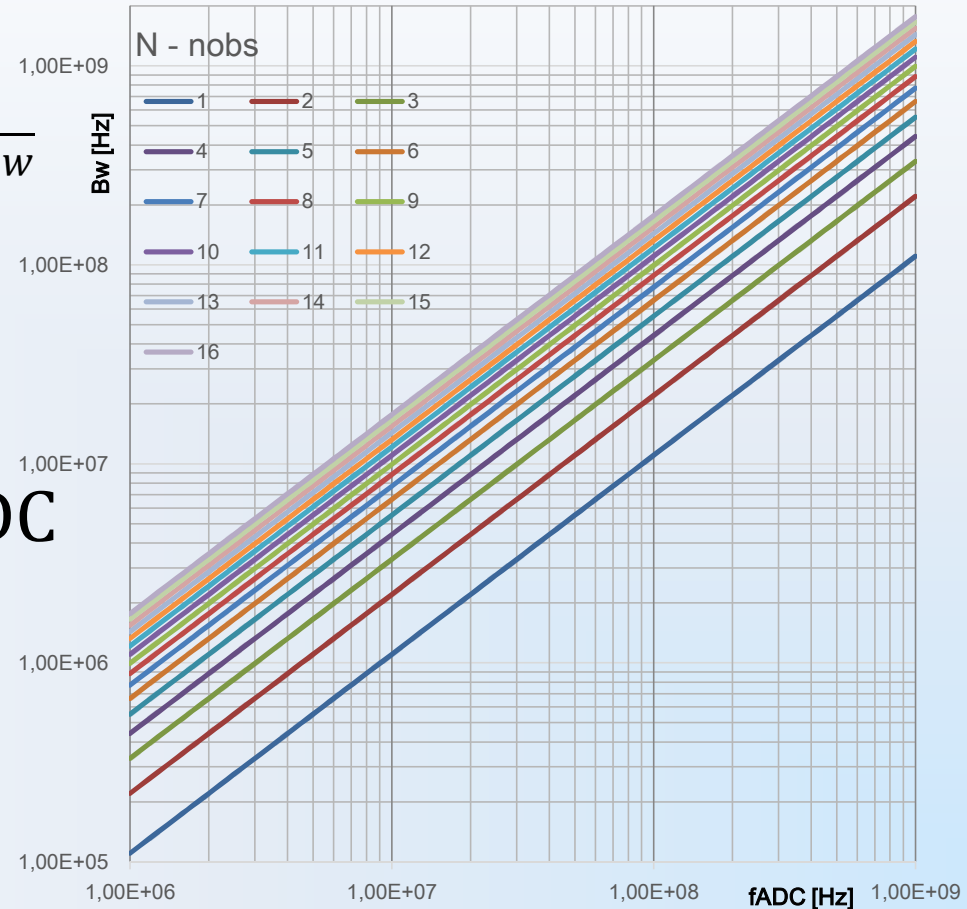
$$\tau = \frac{1}{2\pi \cdot Bw}$$

The required bandwidth  $Bw$  becomes:

$$Bw \geq \frac{\ln(2)}{2\pi} \cdot n \cdot f_{\text{ADC}}$$

In case of AGIPD:

- Digitising 2 values/pixel (gain & amplitude)
- 1024 pixel/port
- @ 33MHz
- ⇒ 16 kHz frame rate

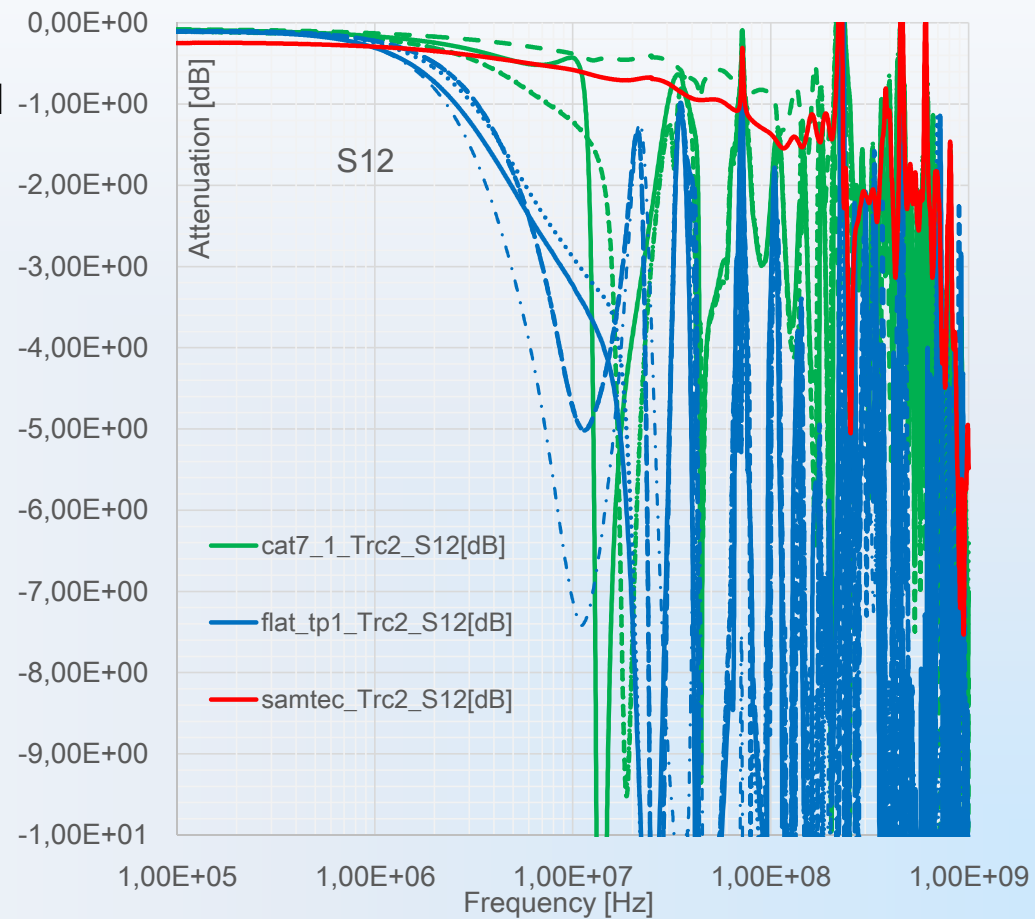


# Going Faster: Limits of Analogue Readout



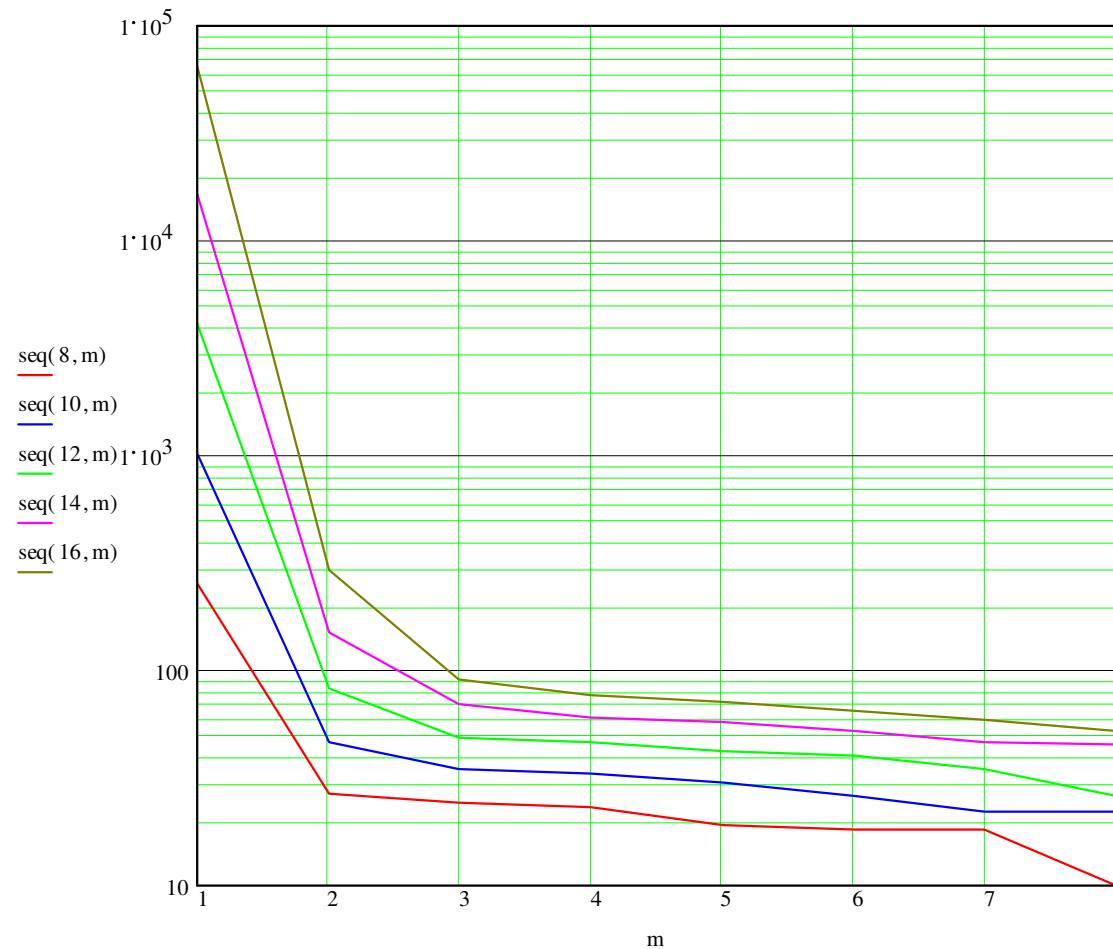
## 2<sup>nd</sup> Order Effects:

- Skin-Effect (att.  $\sim \sqrt{f}$ )
    - can not be compensated with pre-emphasis ( $\sim 1/f$ )
    - can be compensated with a digital (FIR) filter
  - Reflections due to
    - Connectors
    - Bending of cables
- ⇒ Very delicate above a few 10MHz
- ⇒ the same transmission line would be OK for the resulting digital data





## In-pixel digitisation architectures



### $n^{\text{th}}$ Order Bitstream ( $\Delta\Sigma$ )

16

$f_{\text{frame}}$

$$\geq \sqrt[n]{2^{\text{NoB}}} \times f_{\text{frame}}$$

$$\geq \sqrt[n]{2^{\text{NoB}}} \times f_{\text{frame}}$$

(before decimation filter)

Intrinsic

??(overhead)

(yes, digital)

Decimation filter, gain, (pulse shape analysis)

Simple analogue circuit,  
Low/no matching issues,  
noise shaping possible

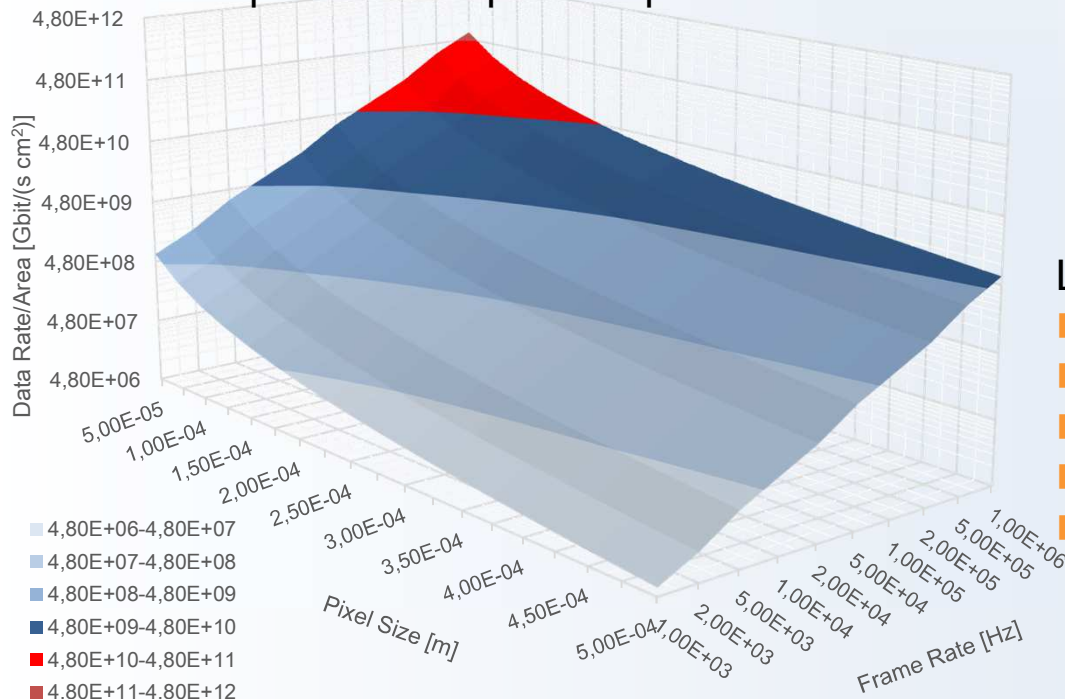
Speed requirements,  
clock distribution,  
readout bandwidth

# Going Faster: Speed Limits

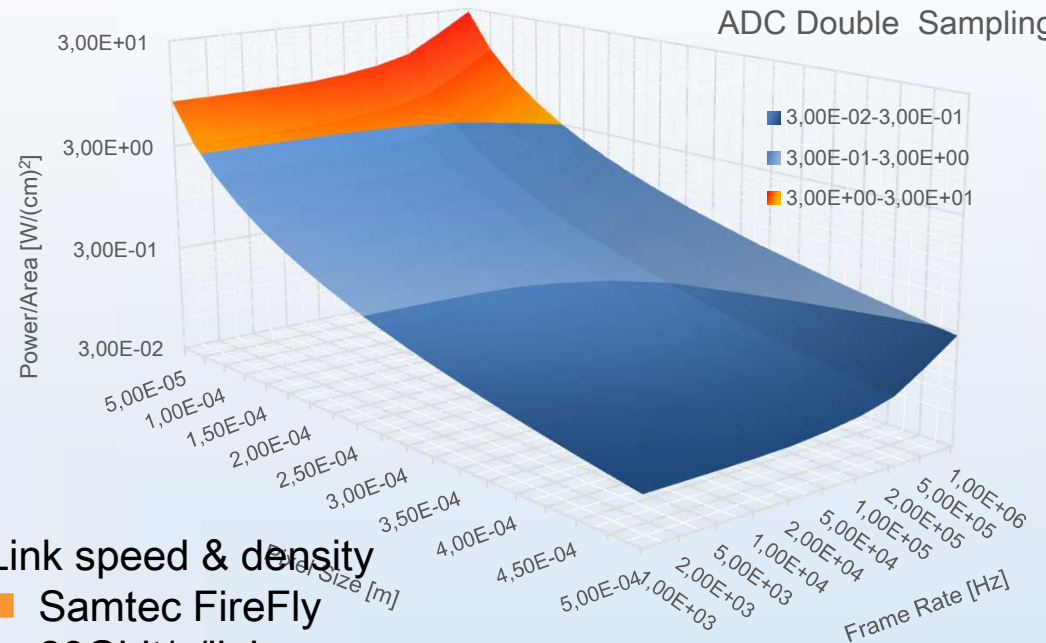


## Power/area

- Dynamic gain switching
- Pixel size 50 $\mu$ m...500 $\mu$ m
- Digitisation with 16 bits
- at a frame rate of  $f_{ADC}$
- Assumption:  $P=200\mu$ W+500pW/Hz



## ADC Double Sampling



## Link speed & density

- Samtec FireFly
- 28Gbit/s/link
- 24Gbit/s/link (net)
- 12 links/unit
- Footprint 20 x 30 mm<sup>2</sup>
  - 48Gbit/(s cm<sup>2</sup>)
  - 3Gs/(s cm<sup>2</sup>) (16bit/sample)
  - DAQ and analysis become „Big Data“ challenges

# Summary & Outlook

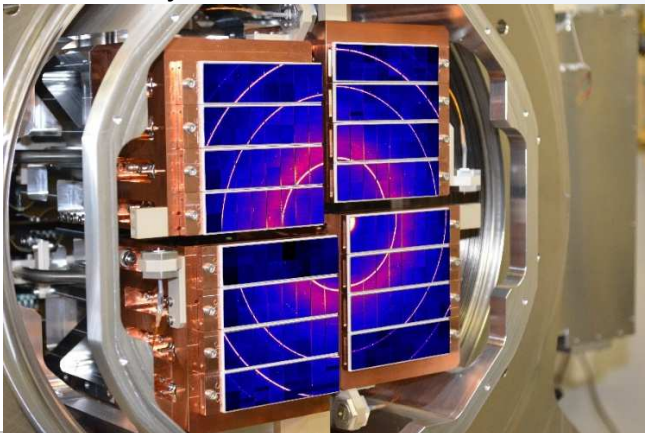


## AGIPD 1.1 (SPB/MID)

- System fulfils all requirements, esp. in terms of
  - Noise ( $<310e$  /  $<1.2$  keV)
  - Single photon sensitivity
  - Dynamic range ( $>10^4\gamma$  @ 12.4keV)
  - Speed
- Both systems in user operation
- Issues with low/med gain discrimination
  - Mask fix (AGIPD 1.2) taped out 14. Aug. 2018
  - $\approx 30\%$  better 'gain separation' in wafer test
  - Module production at IZM & ADVACAM under way

## SFX AGIPD 4M and HiBEF 1M systems

- SW/FW development in progress
- Evaluation of advanced cooling concepts
- Both systems will be delivered with Silicon sensors & AGIPD 1.x ASICs



[http://photon-science.desy.de/research/technical\\_groups/detectors/projects/agipd](http://photon-science.desy.de/research/technical_groups/detectors/projects/agipd)

## ecAGIPD for HiBEF

- Will replace Silicon sensors with High-Z ones
- Changes
  - Electron collecting preamp
  - Reversed polarity of discriminator
  - New calibration circuit
  - Use of twin wells
  - Reversed gain encoding levels
- AGIPD06
  - 16 x16 ecAGIPD prototype
  - Submitted 13.11.2017
  - Manufacturing @ GF only started end of March (30.03.18)
  - Silicon back since July
  - Working, characterisation ongoing
- Only peripheral routing missing for an 64x64 EcAGIPD

## 100kHz Imager for CW-XFEL and PETRA IV

- Concept studies
  - Dynamic gain switching
  - In-pixel ADC
  - High-speed serial link I/O
- More specs needed